DISCRETE SEMICONDUCTORS

DATA SHEET

PEMD13; **PUMD13** NPN/PNP resistor-equipped transistors; R1 = 4.7 kΩ, R2 = 47 kΩ

Product specification Supersedes data of 2001 Feb 27 2003 Oct 08





NPN/PNP resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 47 k Ω

PEMD13; PUMD13

FEATURES

- · Built-in bias resistors
- · Simplified circuit design
- Reduction of component count
- · Reduced pick and place costs.

APPLICATIONS

- · Low current peripheral driver
- Replacement of general purpose transistors in digital applications
- Control of IC inputs.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	TYP.	MAX.	UNIT
V _{CEO}	collector-emitter voltage	_	50	V
Io	output current (DC)	_	100	mA
TR1	NPN	_	_	_
TR2	PNP	_	_	_
R1	bias resistor	4.7	_	kΩ
R2	bias resistor	47	-	kΩ

DESCRIPTION

NPN/PNP resistor-equipped transistors (see "Simplified outline, symbol and pinning" for package details).

PRODUCT OVERVIEW

TYPE	PAC	KAGE	MARKING CODE	PNP/PNP	NPN/NPN	
NUMBER	PHILIPS	EIAJ	WARRING CODE	COMPLEMENT COMPLET		
PEMD13	SOT666		Z1	PEMB13	PEMH13	
PUMD13	SOT363	SC-88	3*1 ⁽¹⁾	PUMB13	PUMH13	

Note

- 1. * = p: Made in Hong Kong.
 - * = t: Made in Malaysia.
 - * = W: Made in China.

SIMPLIFIED OUTLINE, SYMBOL AND PINNING

TYPE NUMBER	SIMPLIFIED OUTLINE AND SYMBOL		PINNING		
I TPE NUMBER	SIMPLIFIED OUTLINE AND STIMBOL	PIN	DESCRIPTION		
PEMD13	6 5 4	1	emitter TR1		
PUMD13	6 5 4	2	base TR1		
	R1 R2	3	collector TR2		
	TR2	4	emitter TR2		
	TR1	5	base TR2		
		6	collector TR1		
	1 2 3				
	1 2 3 Top view MAM468				

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ORDERING INFORMATION

TYPE NUMBER		PACKAGE			
I TPE NOWIBER	NAME	DESCRIPTION	VERSION		
PEMD13	-	plastic surface mounted package; 6 leads	SOT666		
PUMD13	_	plastic surface mounted package; 6 leads	SOT363		

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT		
Per transist	Per transistor; for the PNP transistor with negative polarity						
V _{CBO}	collector-base voltage	open emitter	_	50	V		
V _{CEO}	collector-emitter voltage	open base	_	50	V		
V_{EBO}	emitter-base voltage	open collector	_	10	V		
VI	input voltage TR1						
	positive		_	+30	V		
	negative		_	-5	V		
V _I	input voltage TR2						
	positive		_	+5	V		
	negative		_	-30	V		
I _O	output current (DC)		_	100	mA		
I _{CM}	peak collector current		_	100	mA		
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C					
	SOT363	note 1	_	200	mW		
	SOT666	notes 1 and 2	_	200	mW		
T _{stg}	storage temperature		-65	+150	°C		
Tj	junction temperature		_	150	°C		
T _{amb}	operating ambient temperature		-65	+150	°C		
Per device							
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C					
	SOT363	note 1	_	300	mW		
	SOT666	notes 1 and 2	_	300	mW		

Notes

- 1. Device mounted on an FR4 printed-circuit board, single-sided copper, standard footprint.
- 2. Reflow soldering is the only recommended soldering method.

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
Per transist	or			
R _{th j-a}	thermal resistance from junction to ambient	T _{amb} ≤ 25 °C		
	SOT363	note 1	625	K/W
	SOT666	notes 1 and 2	625	K/W
Per device				
R _{th j-a}	thermal resistance from junction to ambient	T _{amb} ≤ 25 °C		
	SOT363	note 1	416	K/W
	SOT666	notes 1 and 2	416	K/W

Notes

- 1. Device mounted on an FR4 printed-circuit board, single-sided copper, standard footprint.
- 2. Reflow soldering is the only recommended soldering method.

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	. PARAMETER CONDITIONS		MIN.	TYP.	MAX.	UNIT
Per transis	Per transistor; for the PNP transistor with negative polarity					
I _{CBO}	collector-base cut-off current	V _{CB} = 50 V; I _E = 0	_	_	100	nA
I _{CEO}	collector-emitter cut-off current	V _{CE} = 30 V; I _B = 0	_	_	1	μΑ
		V _{CE} = 30 V; I _B = 0; T _j = 150 °C	_	_	50	μΑ
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0	_	_	170	μΑ
h _{FE}	DC current gain	V _{CE} = 5 V; I _C = 10 mA	100	_	_	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 5 \text{ mA}; I_B = 0.25 \text{ mA}$	_	_	100	mV
$V_{i(off)}$	input-off voltage	$I_C = 100 \mu\text{A}; V_{CE} = 5 \text{V}$	_	0.6	0.5	٧
V _{i(on)}	input-on voltage	$I_C = 5 \text{ mA}; V_{CE} = 0.3 \text{ V}$	1.3	0.9	_	٧
R1	input resistor		3.3	4.7	6.1	kΩ
R2 R1	resistor ratio		8	10	12	
C _c	collector capacitance	$I_E = i_e = 0$; $V_{CB} = 10 \text{ V}$; $f = 1 \text{ MHz}$				
	TR1 (NPN)		_	_	2.5	pF
	TR2 (PNP)		_	_	3	pF

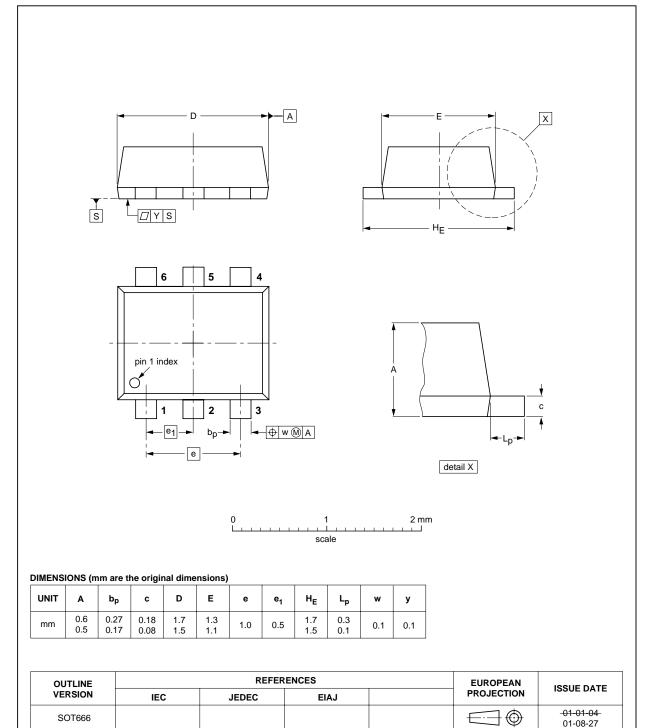
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PACKAGE OUTLINES

Plastic surface mounted package; 6 leads

SOT666

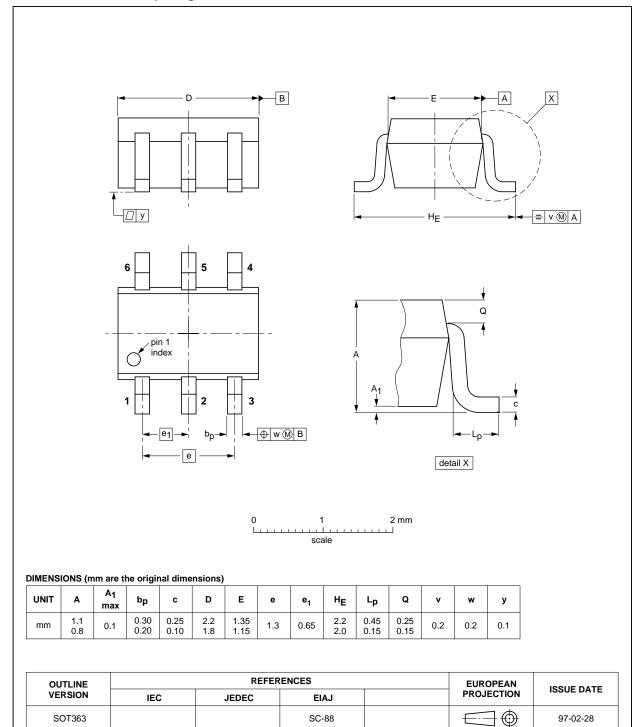


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DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS(2)(3)	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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Contact information

For additional information please visit http://www.semiconductors.philips.com. Fax: +31 40 27 24825 For sales offices addresses send e-mail to: sales.addresses@www.semiconductors.philips.com.

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